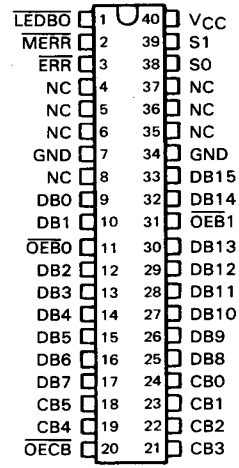
D2840, APRIL 1984—REVISED SEPTEMBER 1985

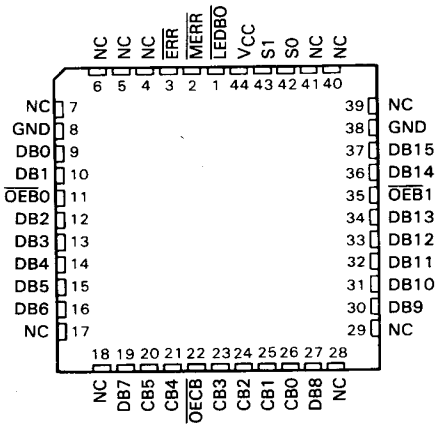
- **Detects and Corrects Single-Bit Errors**
- **Detects and Flags Dual-Bit Errors**
- **Built-In Diagnostic Capability**
- **Fast Write and Read Cycle Processing Times**
- **Byte-Write Capability**
- **Dependable Texas Instruments Quality and Reliability**

DEVICE	OUTPUT
'ALS616	3-State
'ALS617	Open-Collector

SN54ALS616, SN54ALS617 . . . JD PACKAGE
SN74ALS616, SN74ALS617 . . . JD OR N PACKAGE
(TOP VIEW)



SN74ALS616, SN74ALS617 . . . FN PACKAGE
(TOP VIEW)



NC—No internal connection

description

The 'ALS616 and 'ALS617 are 16-bit parallel error detection and correction circuits in 40-pin, 600-mil packages. The EDACs use a modified Hamming code to generate a 6-bit check word from a 16-bit data word. This check word is stored along with the data word during the memory write cycle. During memory read cycles, the 22-bit words from memory are processed by the EDACs to determine if errors have occurred in memory.

Single-bit errors in the 16-bit data word are flagged and corrected. Single-bit errors in the 6-bit check word are flagged, but the data word will remain unaltered. The 6-bit error syndrome code will pinpoint the error-generating location.

Dual-bit errors are flagged but not corrected. These errors may occur in any two bits of the 22-bit word from memory. The gross-error condition of all lows or all highs from memory will be detected. Otherwise, errors in three or more bits of the 22-bit word are beyond the capabilities of these devices to detect.

Read-modify-write (byte-control) operations can be performed with the 'ALS616 and 'ALS617 EDACs by using output latch enable, $\overline{\text{LEDBO}}$, and individual $\overline{\text{OEB0}}$ and $\overline{\text{OEB1}}$ byte control pins.

Diagnostics are performed on the EDACs by controls and internal paths that allow the user to read the contents of the DB and CB input latches. These will determine if the failure occurred in memory or in the EDAC.

The SN54ALS616 and SN54ALS617 are characterized for operation over the full military temperature range of −55°C to 125°C. The SN74ALS616 and SN74ALS617 are characterized for operation from 0°C to 70°C.

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TABLE 1. WRITE CONTROL FUNCTION

MEMORY CYCLE	EDAC FUNCTION	CONTROL S1	CONTROL S0	DATA I/O	DB CONTROL $\overline{OEB0}$ & $\overline{OEB1}$	DB OUTPUT LATCH $\overline{LEDB0}$	CHECK I/O	CB CONTROL $\overline{OECB}$	ERROR FLAGS $\overline{ERR}$	ERROR FLAGS $\overline{MERR}$
Write	Generate check word	L	L	Input	H	X	Output check bits†	L	H	H

†See Table 2 for details on check bit generation.

memory write cycle details

During a memory write cycle, the check bits (CB0 thru CB5) are generated internally in the EDAC by six 8-input parity generators using the 16-bit data word as defined in Table 2. These six check bits are stored in memory along with the original 16-bit data word. This 22-bit word will later be used in the memory read cycle for error detection and correction.

TABLE 2. PARITY ALGORITHM

CHECK WORD BIT	16-BIT DATA WORD 15	14	13	12	11	10	9	8	7	6	5	4	3	2	1	0
CB0			X		X	X	X			X			X		X	X
CB1		X		X		X	X	X				X		X		X
CB2	X			X	X			X	X		X			X	X	
CB3	X	X	X				X	X			X	X	X			
CB4	X	X	X	X	X	X			X	X						
CB5									X	X	X	X	X	X	X	X

The six check bits are parity bits derived from the matrix of data bits as indicated by "X" for each bit.

error detection and correction details

During a memory read cycle, the 6-bit check word is retrieved along with the actual data. In order to be able to determine whether the data from memory is acceptable to use as presented to the bus, the error flags must be tested to determine if they are at the high level.

The first case in Table 3 represents the normal, no-error conditions. The EDAC presents highs on both flags. The next two cases of single-bit errors give a high on $\overline{MERR}$ and a low on $\overline{ERR}$, which is the signal for a correctable error, and the EDAC should be sent through the correction cycle. The last three cases of double-bit errors will cause the EDAC to signal lows on both $\overline{ERR}$ and $\overline{MERR}$, which is the interrupt indication for the CPU.

TABLE 3. ERROR FUNCTION

TOTAL NUMBER OF ERRORS 16-BIT DATA WORD	TOTAL NUMBER OF ERRORS 6-BIT CHECK WORD	ERROR FLAGS $\overline{ERR}$	ERROR FLAGS $\overline{MERR}$	DATA CORRECTION
0	0	H	H	Not applicable
1	0	L	H	Correction
0	1	L	H	Correction
1	1	L	L	Interrupt
2	0	L	L	Interrupt
0	2	L	L	Interrupt

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TABLE 4. READ, FLAG, AND CORRECT FUNCTION

MEMORY CYCLE	EDAC FUNCTION	CONTROL S1	CONTROL S0	DATA I/O	DB CONTROL $\overline{OEB0}$ & $\overline{OEB1}$	DB OUTPUT LATCH $\overline{LEDBO}$	CHECK I/O	CB CONTROL $\overline{OECB}$	ERROR FLAGS $\overline{ERR}$ $\overline{MERR}$
Read	Read & flag	H	L	Input	H	X	Input	H	Enabled†
Read	Latch input data & check bits	H	H	Latched input data	H	L	Latched input check word	H	Enabled†
Read	Output corrected data and syndrome bits	H	H	Output corrected data word	L	X	Output syndrome bits‡	L	Enabled†

†See Table 3 for error description.
‡See Table 5 for error location.

Error detection is accomplished as the 6-bit check word and the 16-bit data word from memory are applied to the internal parity generators/checkers. If the parity of all six groupings of data and check bits are correct, it is assumed that no error has occurred and both error flags will be high.

If the parity of one or more of the check groups is incorrect, an error has occurred and the proper error flag or flags will be set low. The two-bit error is not correctable since the parity tree can only identify single-bit errors. Both error flags are set low when any two-bit error is detected.

Three or more simultaneous bit errors can cause the EDAC to believe that no error, a correctable error, or an uncorrectable error has occurred and will produce erroneous results in all three cases. It should be noted that the gross-error conditions of all highs will be detected.

As the corrected word is made available on the data I/O port (DB0 thru DB15), the check word I/O port (CB0 thru CB5) presents a 6-bit syndrome error code. This syndrome code can be used to locate the bad memory chip. See Table 5 for syndrome decoding.

TABLE 5. SYNDROME DECODING

SYNDROME BITS						ERROR
5	4	3	2	1	0	
L	L	L	L	L	L	2-bit
L	L	L	L	L	H	unc
L	L	L	L	H	L	unc
L	L	L	L	H	H	2-bit
L	L	L	H	L	L	unc
L	L	L	H	L	H	2-bit
L	L	L	H	H	L	2-bit
L	L	L	H	H	H	unc
L	L	H	L	L	L	unc
L	L	H	L	L	H	2-bit
L	L	H	L	H	L	2-bit
L	L	H	L	H	H	DB7
L	L	H	H	L	L	2-bit
L	L	H	H	L	H	unc
L	L	H	H	H	L	DB6
L	L	H	H	H	H	2-bit

SYNDROME BITS						ERROR
5	4	3	2	1	0	
L	H	L	L	L	L	unc
L	H	L	L	L	H	2-bit
L	H	L	L	H	L	2-bit
L	H	L	L	H	H	DB5
L	H	L	H	L	L	2-bit
L	H	L	H	L	H	DB4
L	H	L	H	H	L	DB3
L	H	L	H	H	H	2-bit
L	H	H	L	L	L	2-bit
L	H	H	L	L	H	DB2
L	H	H	L	H	L	DB1
L	H	H	L	H	H	2-bit
L	H	H	H	L	L	DB0
L	H	H	H	L	H	2-bit
L	H	H	H	H	L	2-bit
L	H	H	H	H	H	CB5

SYNDROME BITS						ERROR
5	4	3	2	1	0	
H	L	L	L	L	L	unc
H	L	L	L	L	H	2-bit
H	L	L	L	H	L	2-bit
H	L	L	L	H	H	DB15
H	L	L	H	L	L	2-bit
H	L	L	H	L	H	DB14
H	L	L	H	H	L	DB13
H	L	L	H	H	H	2-bit
H	L	H	L	L	L	2-bit
H	L	H	L	L	H	DB12
H	L	H	L	H	L	DB11
H	L	H	L	H	H	2-bit
H	L	H	H	L	L	DB10
H	L	H	H	L	H	2-bit
H	L	H	H	H	L	2-bit
H	L	H	H	H	H	CB4

SYNDORME BITS						ERROR
5	4	3	2	1	0	
H	H	L	L	L	L	2-bit
H	H	L	L	L	H	DB8
H	H	L	L	H	L	unc
H	H	L	L	H	H	2-bit
H	H	L	H	L	L	DB9
H	H	L	H	L	H	2-bit
H	H	L	H	H	L	2-bit
H	H	L	H	H	H	CB3
H	H	H	L	L	L	unc
H	H	H	L	L	H	2-bit
H	H	H	L	H	L	2-bit
H	H	H	L	H	H	CB2
H	H	H	H	L	L	2-bit
H	H	H	H	L	H	CB1
H	H	H	H	H	L	CB0
H	H	H	H	H	H	none

CB X = error in check bit X
DB Y = error in data bit Y
2-bit = double-bit error
unc = uncorrectable multibit error

read-modify-write (byte control) operations

The 'ALS616 and 'ALS617 devices are capable of byte-write operations. The 22-bit word from memory must first be latched into the DB and CB input latches. This is easily accomplished by switching from the read and flag mode (S1 = H, S0 = L) to the latch input mode (S1 = H, S0 = H). The EDAC will then make any corrections, if necessary, to the data word and place it at the input of the output data latch. This data word must then be latched into the output data latch by taking $\overline{\text{LEDBO}}$ from a low to a high.

Byte control can now be employed on the data word through the $\overline{\text{OEB0}}$ or $\overline{\text{OEB1}}$ controls. $\overline{\text{OEB0}}$ controls DB0-DB7 (byte 0), $\overline{\text{OEB1}}$ controls DB8-DB15 (byte 1).

Placing a high on the byte control will disable the output and the user can modify the byte. If a low is placed on the byte control, then the original byte is allowed to pass onto the data bus unchanged. If the original data word is altered through byte control, a new check word must be generated before it is written back into memory. This is easily accomplished by taking control S1 and S0 low. Table 6 lists the read-modify-write functions.

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TABLE 6. READ-MODIFY-WRITE FUNCTION

MEMORY CYCLE	EDAC FUNCTION	CONTROL S1	CONTROL S0	BYTEn†	$\overline{OEB}$n†	DB OUTPUT LATCH $\overline{LEDBO}$	CHECK I/O	CB CONTROL	ERROR FLAG $\overline{ERR}$	ERROR FLAG $\overline{MERR}$
Read	Read & Flag	H	L	Input	H	X	Input	H	Enabled	
Read	Latch input data & check bits	H	H	Latched Input data	H	L	Latched input check word	H	Enabled	
Read	Latch corrected data word into output latch	H	H	Latched output data word	H	H	Hi-Z	H	Enabled	
							Output Syndrome bits	L		
Modify/ write	Modify appropriate byte or bytes & generate new check word	L	L	Input modified BYTE0	H	H	Output check word	L	H	H
				Output unchanged BYTE0	L					

†$\overline{OEB}$0 controls DB0-DB7 (BYTE0), $\overline{OEB}$1 controls DB8-DB15 (BYTE1)

diagnostic operations

The 'ALS616 and 'ALS617 are capable of diagnostics that allow the user to determine whether the EDAC or the memory is failing. The diagnostic function tables will help the user to see the possibilities for diagnostic control.

In the diagnostic mode (S1 = L, S0 = H), the checkword is latched into the input latch while the data input latch remains transparent. This lets the user apply various data words against a fixed known checkword. If the user applies a diagnostic data word with an error in any bit location, the $\overline{ERR}$ flag should be low. If a diagnostic data word with two errors in any bit location is applied, the $\overline{MERR}$ flag should be low. After the checkword is latched into the input latch, it can be verified by taking $\overline{OECB}$ low. This outputs the latched checkword. The diagnostic data word can be latched into the output data latch and verified via the $\overline{LEDBO}$ control pin. By changing from the diagnostic mode (S1 = L, S0 = H), the user can verify that the EDAC will correct the diagnostic data word. Also, the syndrome bits can be produced to verify that the EDAC pinpoints the error location. Table 7 lists the diagnostic functions.

TABLE 7. DIAGNOSTIC FUNCTION

EDAC FUNCTION	CONTROL S1	CONTROL S0	DATA I/O	DB BYTE CONTROL $\overline{OEB_n}$	DB OUTPUT LATCH $\overline{LEDBO}$	CHECK I/O	CB CONTROL $\overline{OECB}$	ERROR FLAGS $\overline{ERR}$	ERROR FLAGS $\overline{MERR}$
Read & flag	H	L	Input correct data word	H	X	Input correct check bits	H	H	H
Latch input check word while data input latch remains transparent	L	H	Input diagnostic data word†	H	L	Latched input check bits	H	Enabled	
Latch diagnostic data word into output latch	L	H	Input diagnostic data word†	H	H	Output latched check bits	L	Enabled	
						Hi-Z	H		
Latch diagnostic data word into input latch	H	H	Latched input diagnostic data word	H	H	Output syndrome bits	L	Enabled	
						Hi-Z	H		
Output diagnostic data word & syndrome bits	H	H	Output diagnostic data word	L	H	Output syndrome bits	L	Enabled	
						Hi-Z	H		
Output corrected diagnostic data word & output syndrome bits	H	H	Output corrected diagnostic data word	L	L	Output syndrome bits	L	Enabled	
						Hi-Z	H		

†Diagnostic data is a data word with an error in one bit location except when testing the $\overline{MERR}$ error flag. In this case, the diagnostic data word will contain errors in two bit locations.

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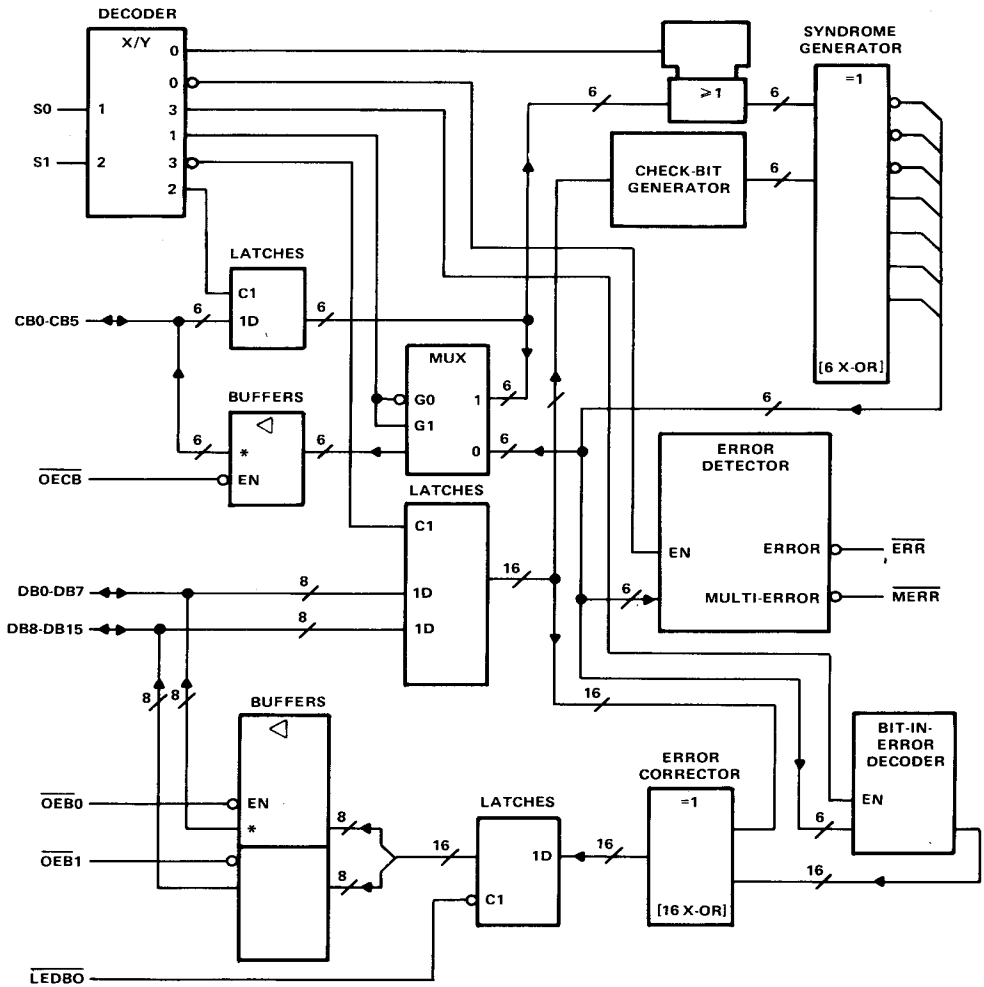
logic diagram (positive logic)



*'ALS616 has 3-state (▽) check-bit and data outputs.
'ALS617 has open-collector(◇) check-bit and data outputs.

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)

Supply voltage, V_{CC} (see Note 1) . . . . . 7 V
Input voltage: CB and DB . . . . . 5.5 V
All others . . . . . 7 V
Operating case temperature range SN54ALS616, SN54ALS617, ... −55°C to 125°C
Operating free-air temperature range, SN74ALS616, SN74ALS617 . . . . . 0°C to 70°C
Storage temperature range . . . . . −65°C to 150°C

recommended operating conditions

			SN54ALS616 SN54ALS617			SN74ALS616 SN74ALS617			UNIT
			MIN	NOM	MAX	MIN	NOM	MAX	
V_{CC}	Supply voltage		4.5	5	5.5	4.5	5	5.5	V
V_{IH}	High-level input voltage		2			2			V
V_{IL}	Low-level input voltage				0.8			0.8	V
V_{OH}	High-level output voltage	DB or CB ’ALS617			5.5			5.5	V
I_{OH}	High-level output current	$\overline{ERR}$ or $\overline{MERR}$			−0.4			−0.4	mA
		DB or CB ’ALS616			−1			−2.6	
I_{OL}	Low-level output current	$\overline{ERR}$ or $\overline{MERR}$			4			8	mA
		DB or CB			12			24	
t_w	Pulse duration	$\overline{LEDBO}$ low	45			25			ns
t_{su}	Setup time	(1) Data and check word before S0↑ (S1 = H)	15			12			ns
		(2) S0 high before $\overline{LEDBO}$↑ (S1 = H)†	45			45			
		(3) $\overline{LEDBO}$ high before the earlier of S0↓ or S1↓†	0			0			
		(4) $\overline{LEDBO}$ high before S1↑ (S0 = H)	0			0			
		(5) Diagnostic data word before S1↑ (S0 = H)	28			12			
		(6) Diagnostic check word before the later of S1↓ or S0↑	15			12			
		(7) Diagnostic data word before $\overline{LEDBO}$↑ (S1 = L and S0 = H)†	35			20			
t_h	Hold time	(8) Read-mode, S0 low and S1 high	35			30			ns
		(9) Data and check word after S0↑ (S1 = H)	20			15			
		(10) Data word after S1↑ (S0 = H)	20			15			
		(11) Check word after the later of S1↓ or S0↑	20			15			
		(12) Diagnostic data word after $\overline{LEDBO}$↑ (S1 = L, S0 = H)‡	0			0			
t_{corr}	Correction time (see Figure 1)		70			65			ns
T_C	Operating case temperature		−55		125				°C
T_A	Operating free-air temperature					0		70	°C

†These times ensure that corrected data is saved in the output data latch.
‡These times ensure that the diagnostic data word is saved in the output data latch.

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'ALS616 electrical characteristics over recommended operating temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		SN54ALS616 MIN	SN54ALS616 TYP†	SN54ALS616 MAX	SN74ALS616 MIN	SN74ALS616 TYP†	SN74ALS616 MAX	UNIT
V_{IK}		V_{CC} = 4.5 V,	I_I = −18 mA			−1.5			−1.5	V
V_{OH}	All outputs	V_{CC} = 4.5 V to 5.5 V,	I_{OH} = −0.4 mA	V_{CC}−2			V_{CC}−2			V
	DB or CB	V_{CC} = 4.5 V,	I_{OH} = −1 mA	2.4	3.3					
		V_{CC} = 4.5 V,	I_{OH} = −2.6 mA				2.4	3.2		
V_{OL}	$\overline{ERR}$ or $\overline{MERR}$	V_{CC} = 4.5 V,	I_{OH} = 4 mA		0.25	0.4		0.25	0.4	V
		V_{CC} = 4.5 V,	I_{OL} = 8 mA					0.35	0.5	
	DB or CB	V_{CC} = 4.5 V,	I_{OL} = 12 mA		0.25	0.4		0.25	0.4	
		V_{CC} = 4.5 V,	I_{OL} = 24 mA					0.35	0.5	
I_I	S0 or S1	V_{CC} = 5.5 V,	V_I = 7 V			0.1			0.1	mA
	DB or CB	V_{CC} = 5.5 V,	V_I = 5.5 V			0.1			0.1	
I_{IH}	S0 or S1	V_{CC} = 5.5 V,	V_I = 2.7 V			20			20	μA
	DB or CB‡					20			20	
I_{IL}	S0 or S1	V_{CC} = 5.5 V,	V_I = 0.4 V			−0.4			−0.4	mA
	DB or CB‡					−0.1			−0.1	
I_O§		V_{CC} = 5.5 V,	V_O = 2.25 V	−30		−112	−30		−112	mA
I_{CC}		V_{CC} = 5.5 V	See Note 1		110	190		110	170	mA

†All typical values are at V_{CC} = 5 V, T_A = 25°C.
‡For I/O ports, the parameters I_{IH} and I_{IL} include the off-state output current.
§The output conditions have been chosen to produce a current that closely approximates one half of the true short-circuit output current, I_{OS}.
NOTE 1: I_{CC} is measured with S0 and S1 at 4.5 V and all CB and DB pins grounded.

'ALS616 switching characteristics, V_{CC} = 4.5 V to 5.5 V, C_L = 50 pF, T_C = −55°C to 125°C for SN54ALS616, T_A = 0°C to 70°C for SN74ALS616

PARAMETER	FROM (INPUT)	TO (OUTPUT)	TEST CONDITIONS	SN54ALS616 MIN	SN54ALS616 MAX	SN74ALS616 MIN	SN74ALS616 MAX	UNIT
t_{pd}	DB and CB	$\overline{ERR}$	S1 = H, S0 = L, R_L = 500 Ω	10	43	10	40	ns
	DB	$\overline{ERR}$	S1 = L, S0 = H, R_L = 500 Ω	10	43	10	40	
t_{pd}	DB and CB	$\overline{MERR}$	S1 = H, S0 = L, R_L = 500 Ω	15	65	15	55	ns
	DB	$\overline{MERR}$	S1 = L, S0 = H, R_L = 500 Ω	15	65	15	55	
t_{pd}	S0↓ and S1↓	CB	R1 = R2 = 500 Ω	10	60	10	49	ns
t_{pd}	DB	CB	S1 = L, S0 = L, R1 = R2 = 500 Ω	10	60	10	49	ns
t_{pd}	$\overline{LEDBO}$↓	DB	S1 = X, S0 = H, R1 = R2 = 500 Ω	7	35	7	30	ns
t_{pd}	S1↑	CB	S0 = H, R1 = R2 = 500 Ω	10	50	10	50	ns
t_{en}	$\overline{OECB}$↓	CB	S0 = H, S1 = X, R1 = R2 = 500 Ω	2	30	2	27	ns
t_{dis}	$\overline{OECB}$↑	CB	S0 = H, S1 = X, R1 = R2 = 500 Ω	2	30	2	27	ns
t_{en}	$\overline{OEB0}$ and $\overline{OEB1}$↓	DB	S0 = H, S1 = X, R1 = R2 = 500 Ω	2	30	2	27	ns
t_{dis}	$\overline{OEB0}$ and $\overline{OEB1}$↑	DB	S0 = H, S1 = X, R1 = R2 = 500 Ω	2	30	2	27	ns

'ALS617 electrical characteristics over recommended operating temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		SN54ALS617			SN74ALS617			UNIT
				MIN	TYP†	MAX	MIN	TYP†	MAX	
V_{IK}		V_{CC} = 4.5 V,	I_I = −18 mA			−1.5			−1.5	V
V_{OH}	$\overline{ERR}$ or $\overline{MERR}$	V_{CC} = 4.5 V to 5.5 V,	I_{OH} = −0.4 mA	V_{CC}−2			V_{CC}−2			V
I_{OH}	DB or CB	V_{CC} = 4.5 V,	V_{OH} = 5.5 V			0.1			0.1	mA
V_{OL}	$\overline{ERR}$ or $\overline{MERR}$	V_{CC} = 4.5 V,	I_{OH} = 4 mA		0.25	0.4		0.25	0.4	V
		V_{CC} = 4.5 V,	I_{OL} = 8 mA					0.35	0.5	
	DB or CB	V_{CC} = 4.5 V,	I_{OL} = 12 mA		0.25	0.4		0.25	0.4	
		V_{CC} = 4.5 V,	I_{OL} = 24 mA					0.35	0.5	
I_I	S0 or S1	V_{CC} = 5.5 V,	V_I = 7 V			0.1			0.1	mA
	DB or CB	V_{CC} = 5.5 V,	V_I = 5.5 V			0.1			0.1	
I_{IH}	S0 or S1	V_{CC} = 5.5 V,	V_I = 2.7 V			20			20	μA
	DB or CB‡					20			20	
I_{IL}	S0 or S1	V_{CC} = 5.5 V,	V_I = 0.4 V			−0.4			−0.4	mA
	DB or CB‡					−0.1			−0.1	
I_O§	$\overline{ERR}$ or $\overline{MERR}$	V_{CC} = 5.5 V,	V_O = 2.25 V	−30		−112	−30		−112	mA
I_{CC}		V_{CC} = 5.5 V	See Note 1		110			110		mA

†All typical values are at V_{CC} = 5 V, T_A = 25°C.
‡For I/O ports, the parameters I_{IH} and I_{IL} include the off-state output current.
§The output conditions have been chosen to produce a current that closely approximates one half of the true short-circuit output current, I_{OS}.
NOTE 1: I_{CC} is measured with S0 and S1 at 4.5 V and all CB and DB pins grounded.

'ALS617 switching characteristics, V_{CC} = 4.5 V to 5.5 V, C_L = 50 pF, T_C = −55°C to 125°C for SN54ALS617, T_A = 0°C to 70°C for SN74ALS617

PARAMETER	FROM (INPUT)	TO (OUTPUT)	TEST CONDITIONS	SN54ALS617			SN74ALS617			UNIT
				MIN	TYP†	MAX	MIN	TYP†	MAX	
t_{pd}	DB and CB	$\overline{ERR}$	S1 = H, S0 = L, R_L = 500 Ω		26			26		ns
	DB	$\overline{ERR}$	S1 = L, S0 = H, R_L = 500 Ω		26			26		
t_{pd}	DB and CB	$\overline{MERR}$	S1 = H, S0 = L, R_L = 500 Ω		40			40		ns
			S1 = L, S0 = H, R_L = 500 Ω		40			40		
t_{pd}	S0↓ and S1↓	CB	R_L = 680 Ω		40			40		ns
t_{pd}	DB	CB	S1 = L, S0 = L, R_L = 680 Ω		40			40		ns
t_{pd}	$\overline{LEDBO}$↓	DB	S1 = X, S0 = H, R_L = 680 Ω		26			26		ns
t_{pd}	S1↑	CB	S0 = H, R_L = 680 Ω		40			40		ns
t_{PLH}	$\overline{OECB}$↑	CB	S1 = X, S0 = H, R_L = 680 Ω		24			24		ns
t_{PHL}	$\overline{OECB}$↓	CB	S1 = X, S0 = H, R_L = 680 Ω		24			24		ns
t_{PLH}	$\overline{OEB0}$ and $\overline{OEB1}$↑	DB	S1 = X, S0 = H, R_L = 680 Ω		24			24		ns
t_{PHL}	$\overline{OEB0}$ and $\overline{OEB1}$↓	DB	S1 = X, S0 = H, R_L = 680 Ω		24			24		ns

†All typical values are at V_{CC} = 5 V, T_A = 25°C.

Additional information on these products can be obtained from the factory as it becomes available.

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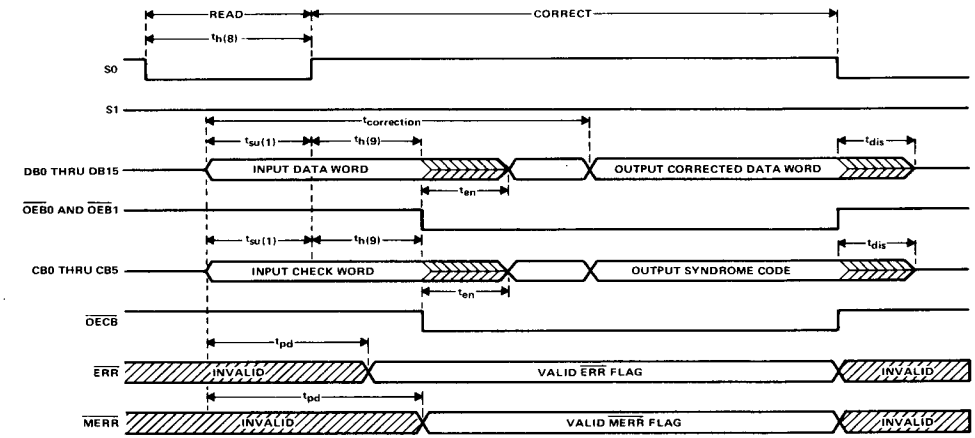

FIGURE 1. READ, FLAG, AND CORRECT MODE SWITCHING WAVEFORMS

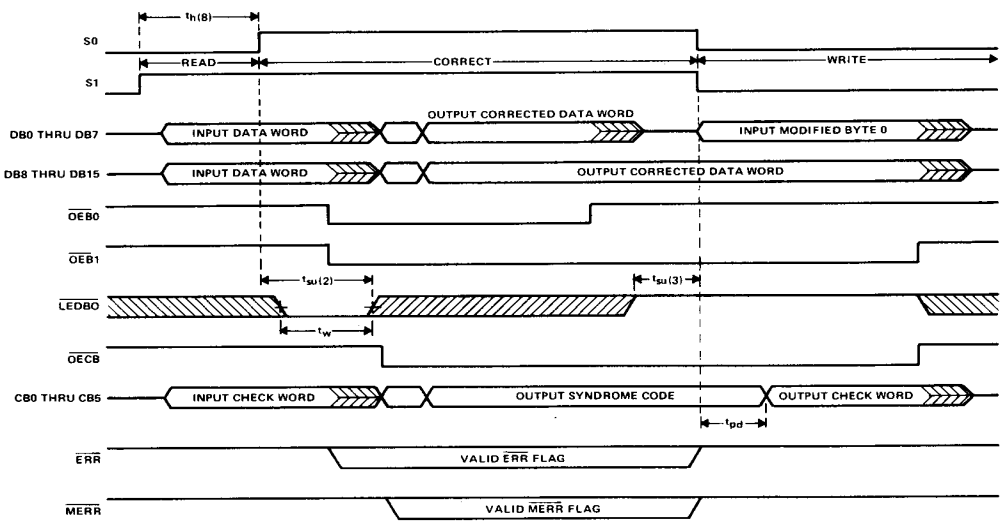

FIGURE 2. READ, CORRECT, MODIFY MODE SWITCHING WAVEFORMS

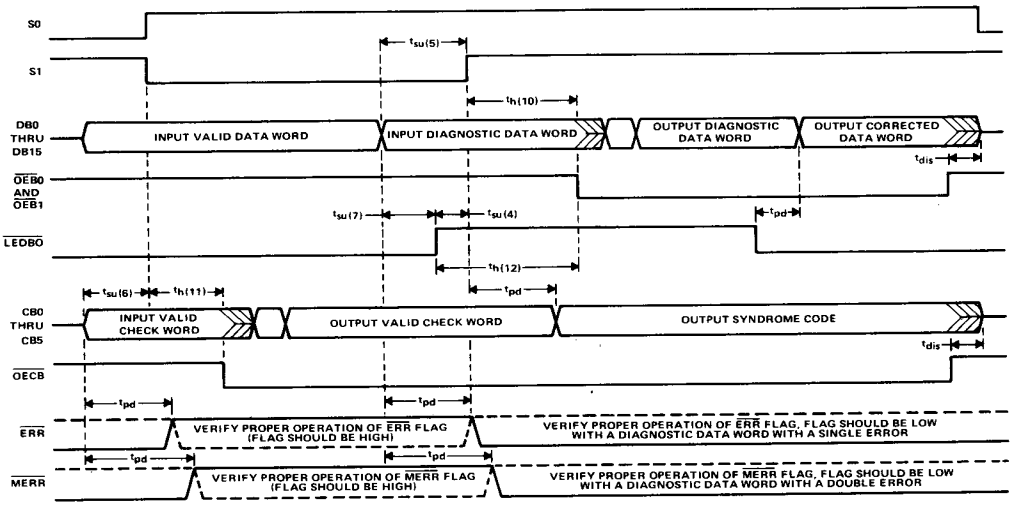

FIGURE 3. DIAGNOSTIC MODE SWITCHING WAVEFORM

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